What is claimed is:

[Claim 1]

A semiconductor memory device, comprising:

a plurality of first electrode layers stacked in a first direction;

a first insulating film provided above an uppermost layer of the plurality of first electrode layers;

a plurality of second electrode layers stacked in the first direction and provided above the first insulating film;

a first columnar body extending through the plurality of first electrode layers in the first direction and including a first charge storage film;

a second columnar body extending through the plurality of second electrode layers in the first direction and including a second charge storage film;

a connection part connecting the first columnar body and the second columnar body, the connection part being provided in the first insulating film and including a third charge storage film, the first to third charge storage films being continuously provided in the first and second columnar bodies and the connection part, the connection part including a first portion having minimum and maximum widths in a second direction crossing the first direction; and

a spacer film provided around the first portion of the connection part and positioned between the first insulating film and the first portion of the connection part,

the first columnar body including a second portion facing the uppermost layer of the plurality of first electrode layers, the second portion of the first columnar body having a first width in the second direction, the first width of the second portion in the first columnar body being greater than the minimum width of the first portion in the connection part,

the second columnar body including a third portion facing a lowermost layer of the plurality of second electrode layers, the third portion of the second columnar body having a second width in the second direction, the second width of the third portion in the second columnar body being less than the maximum width of the first portion in the connection part.

[Claim 2]

The semiconductor memory device according to claim 1, wherein

the first columnar body has a substantially circular configuration in a cross-section orthogonal to the first direction; and

the first columnar body has a center in the cross-section orthogonal to the first direction, the center of the first columnar body being substantially aligned with a center of the spacer film in a cross section orthogonal to the first direction.

[Claim 3]

The semiconductor memory device according to claim 1, wherein

the plurality of first electrode layers includes a first electrode layer provided at the furthest position from the connection part; and

the first columnar body includes a fourth portion extending through the first electrode layer of the plurality of first electrode layers, the fourth portion of the first columnar body having a third width in the second direction, the third width being greater than the minimum width of the connection part.

[Claim 4]

The semiconductor memory device according to claim 1, wherein the second width of the third portion in the second columnar

body is less than the first width of the second portion in the first columnar body.

[Claim 5]

The semiconductor memory device according to claim 1, wherein

the first columnar body and the connection part include an insulating core and a semiconductor film, the insulating core extending in the first direction, the semiconductor film surrounding the insulating core and extending in the first direction; and

the semiconductor film has an outer diameter at the first columnar body and another outer diameter at the connection part, the outer diameter at the first columnar body being greater than a minimum value of said another outer diameter at the connection part.

[Claim 6]

The semiconductor memory device according to claim 1, wherein

the first portion of the connection part has the minimum width at the first columnar body side, and the maximum width at the second columnar body side.